



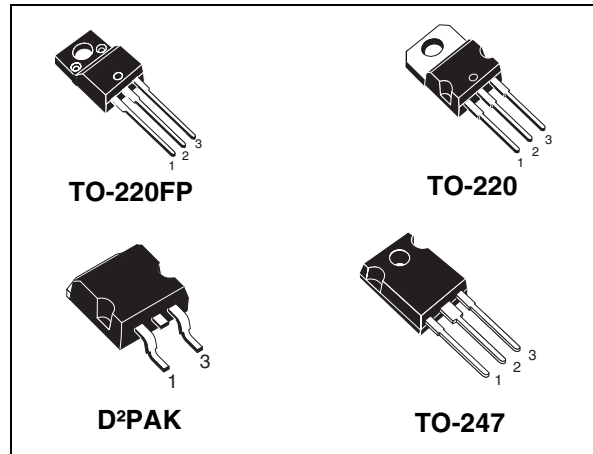
STB28NM50N, STF28NM50N STP28NM50N, STW28NM50N

N-channel 500 V, 0.135 Ω , 21 A D²PAK, TO-220, TO-220FP, TO-247
MDmesh™ II Power MOSFET

Features

Order codes	V _{DSS} (@T _{jmax})	R _{DS(on)} max.	I _D
STB28NM50N	550 V	< 0.158 Ω	21 A
STF28NM50N			
STP28NM50N			
STW28NM50N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram



Table 1. Device summary

Order codes	Marking	Package	Packaging
STB28NM50N	28NM50N	D ² PAK	Tape and reel
STF28NM50N		TO-220FP	Tube
STP28NM50N		TO-220	
STW28NM50N		TO-247	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value				Unit
		TO-220	D ² PAK	TO-247	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	500				V
V_{GS}	Gate- source voltage	± 25				V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	21		21 ⁽¹⁾		A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	13		13 ⁽¹⁾		A
I_{DM} ⁽²⁾	Drain current (pulsed)	84		84 ⁽¹⁾		A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	150		35		W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{ s}; T_C=25\text{ °C}$)			2500		V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15				V/ns
T_{stg}	Storage temperature	- 55 to 150				°C
T_j	Max. operating junction temperature	150				°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 21\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	D ² PAK	TO-247	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	0.83			3.6	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		50	62.5	°C/W
$R_{thj-pcb}$ ⁽¹⁾	Thermal resistance junction-pcb max		30			°C/W
T_l	Maximum lead temperature for soldering purpose	300		300		°C

- When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j\text{ Max}$)	7.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	300	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	500			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}, @125^{\circ}\text{C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25 \text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 10.5 \text{ A}$		0.135	0.158	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz},$ $V_{GS} = 0$	-	1735	-	pF
C_{oss}	Output capacitance			122		pF
C_{rss}	Reverse transfer capacitance			4.3		pF
$C_{oss(eq)}^{(1)}$	Equivalent output capacitance time related	$V_{GS} = 0, V_{DS} = 0 \text{ to } 50 \text{ V}$	-	418	-	pF
Q_g	Total gate charge	$V_{DD} = 400 \text{ V}, I_D = 21 \text{ A},$ $V_{GS} = 10 \text{ V},$ (see Figure 19)	-	50	-	nC
Q_{gs}	Gate-source charge			9.5		nC
Q_{gd}	Gate-drain charge			25		nC
R_g	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain	-	2.7	-	Ω

1. $C_{oss(eq)}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250\text{ V}$, $I_D = 10.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 18)		13.6		ns	
t_r	Rise time			19		ns	
$t_{d(off)}$	Turn-off delay time				62	-	ns
t_f	Fall time				52		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				21	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				84	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 21\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 400\text{ V}$ (see Figure 23)		326		ns
Q_{rr}	Reverse recovery charge				5	μC
I_{RRM}	Reverse recovery current				30	A
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 400\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 23)		376		ns
Q_{rr}	Reverse recovery charge				6.2	μC
I_{RRM}	Reverse recovery current				33.2	A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

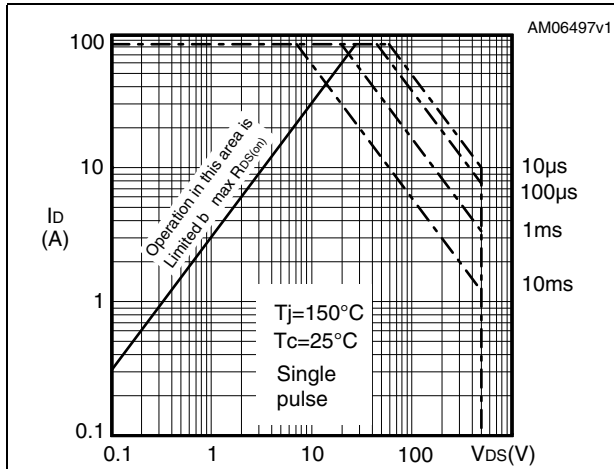


Figure 3. Thermal impedance for TO-220, D²PAK

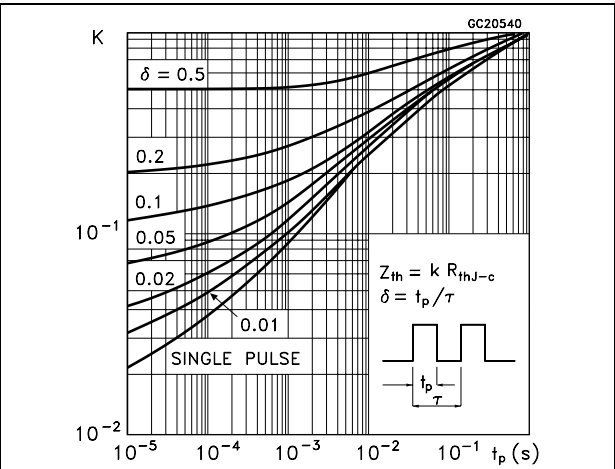


Figure 4. Safe operating area for TO-220FP

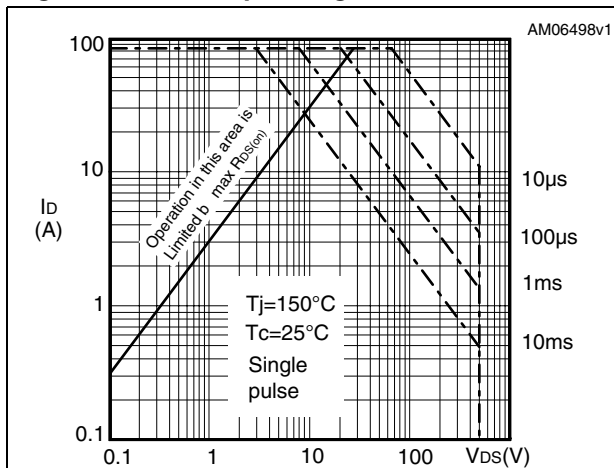


Figure 5. Thermal impedance for TO-220FP

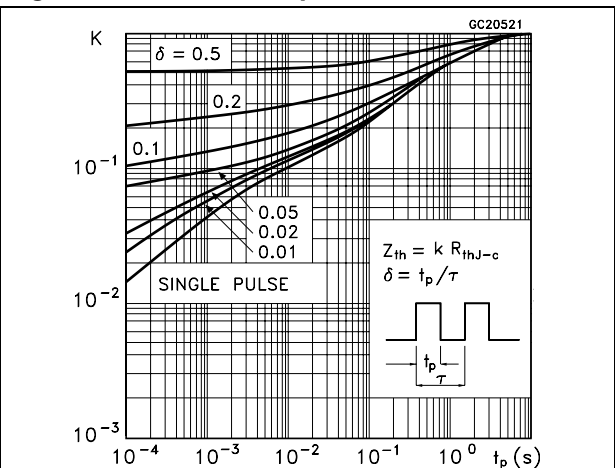


Figure 6. Safe operating area for TO-247

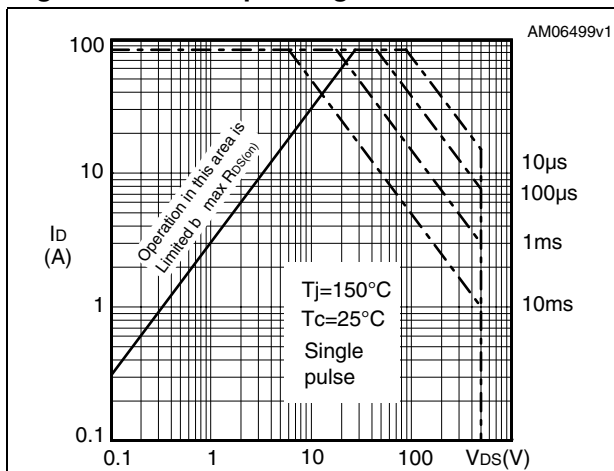


Figure 7. Thermal impedance for TO-247

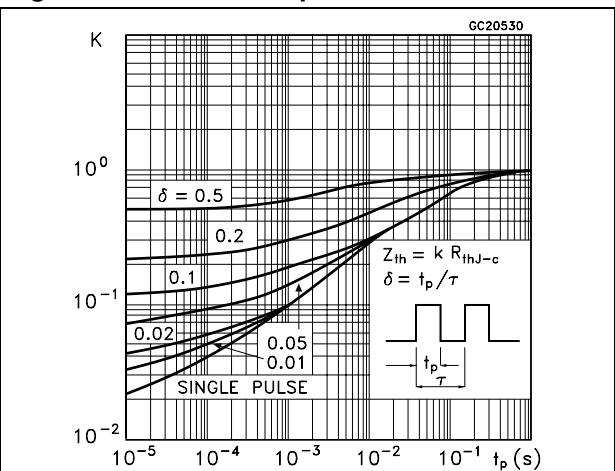


Figure 8. Output characteristics

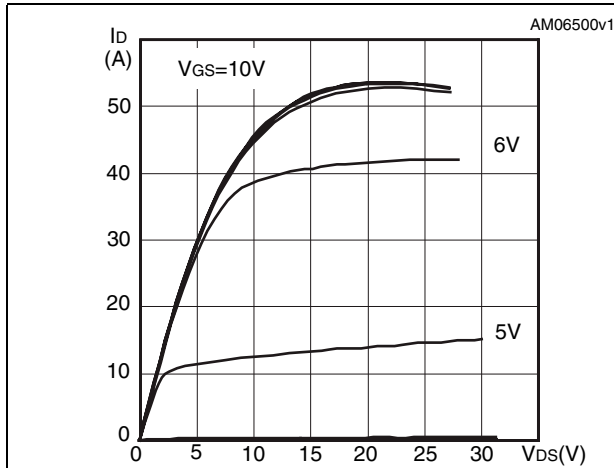


Figure 9. Transfer characteristics

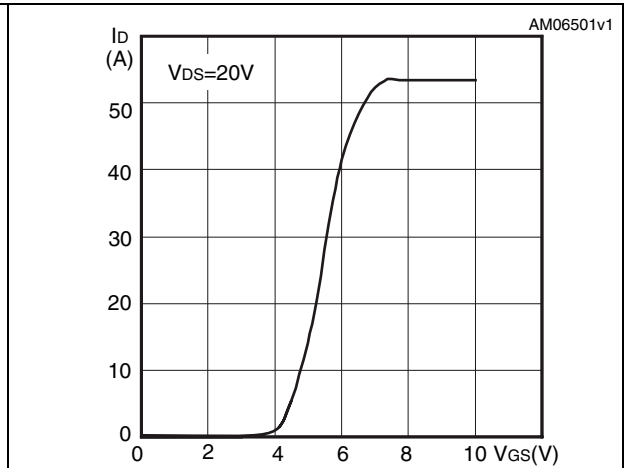


Figure 10. Gate charge vs gate-source voltage Figure 11. Static drain-source on resistance

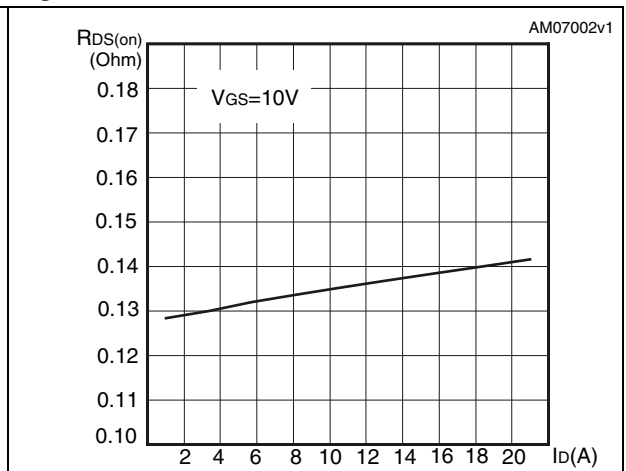
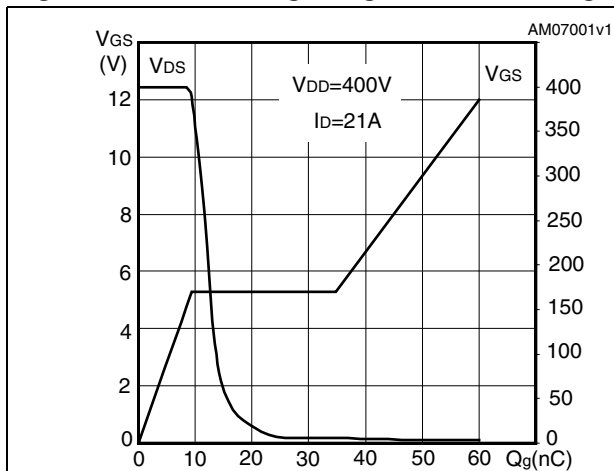


Figure 12. Capacitance variations

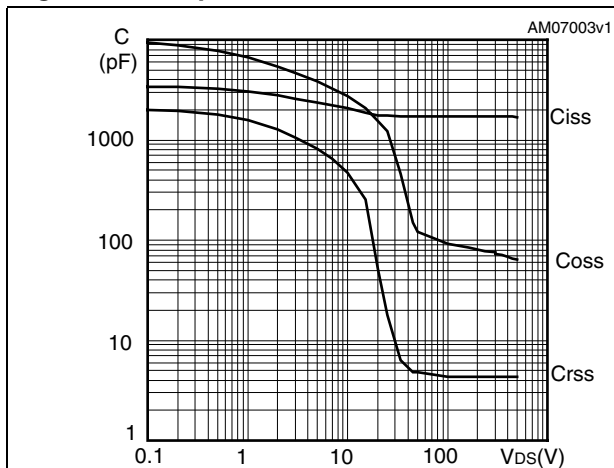


Figure 13. Output capacitance stored energy

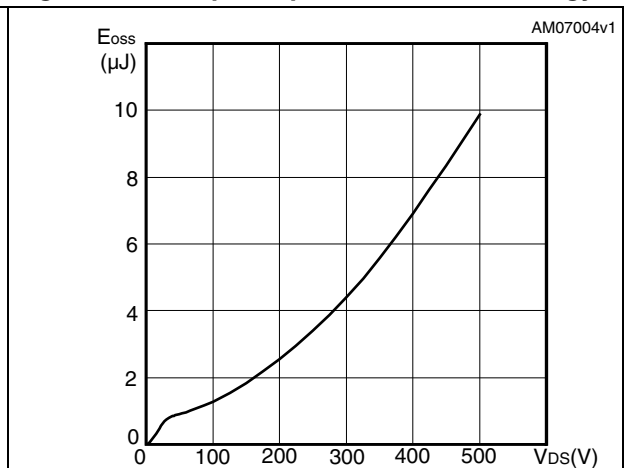


Figure 14. Normalized gate threshold voltage vs temperature

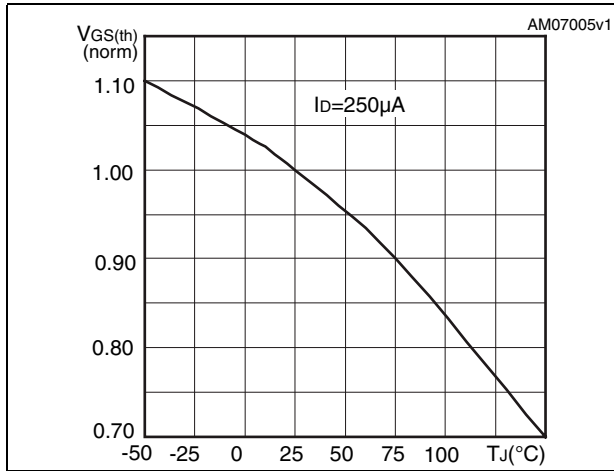


Figure 15. Normalized on resistance vs temperature

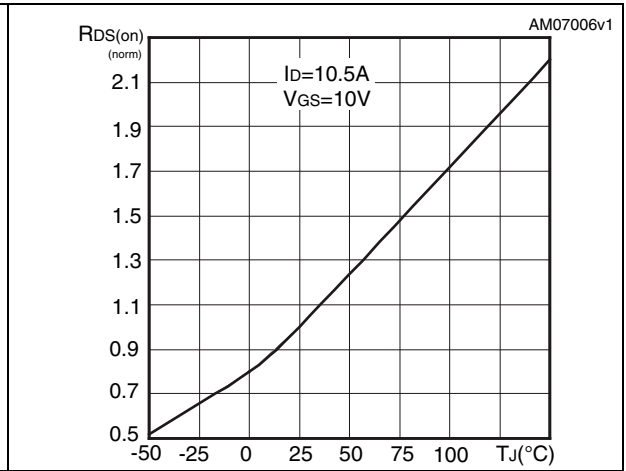


Figure 16. Normalized B_VDSS vs temperature

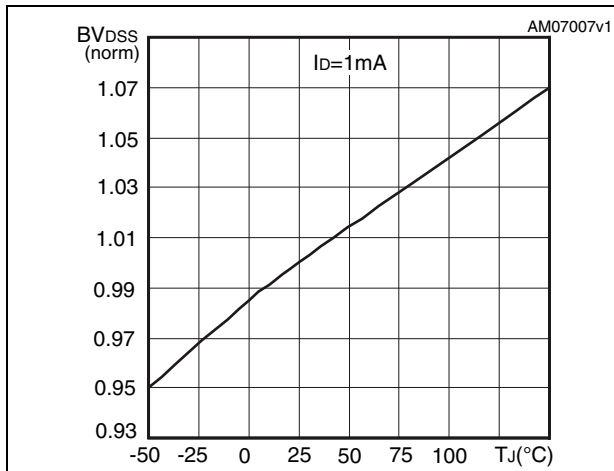
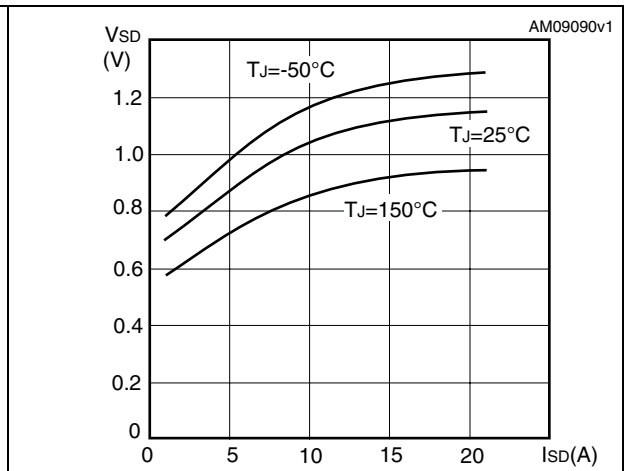


Figure 17. Source-drain diode forward characteristics



3 Test circuits

Figure 18. Switching times test circuit for resistive load

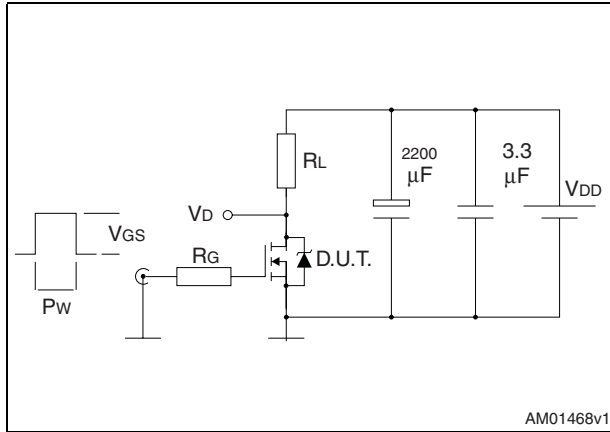


Figure 19. Gate charge test circuit

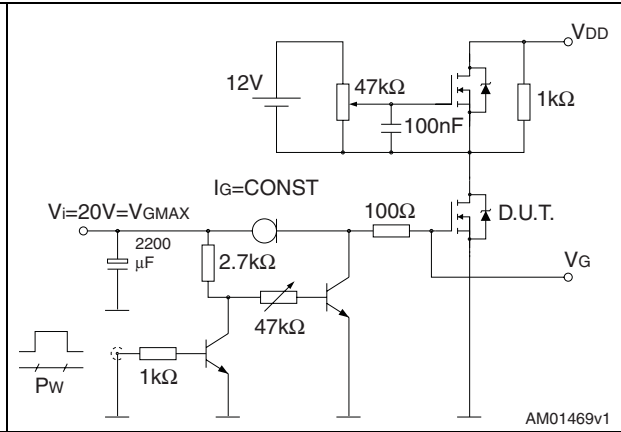


Figure 20. Test circuit for inductive load switching and diode recovery times

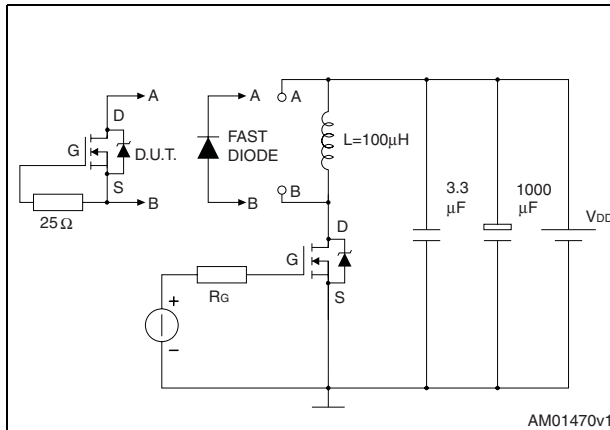


Figure 21. Unclamped inductive load test circuit

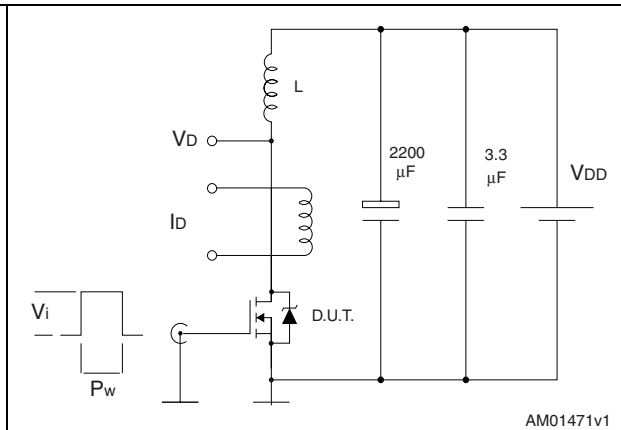


Figure 22. Unclamped inductive waveform

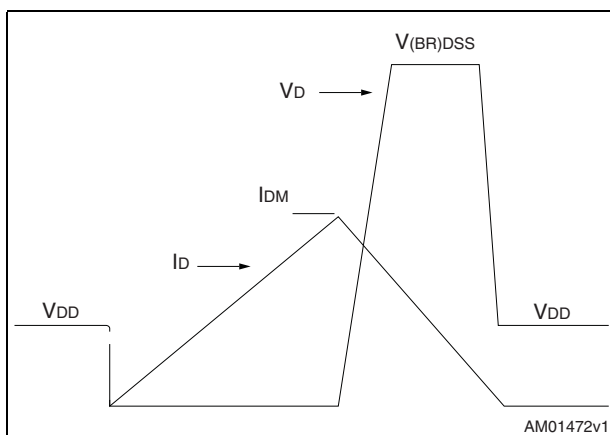
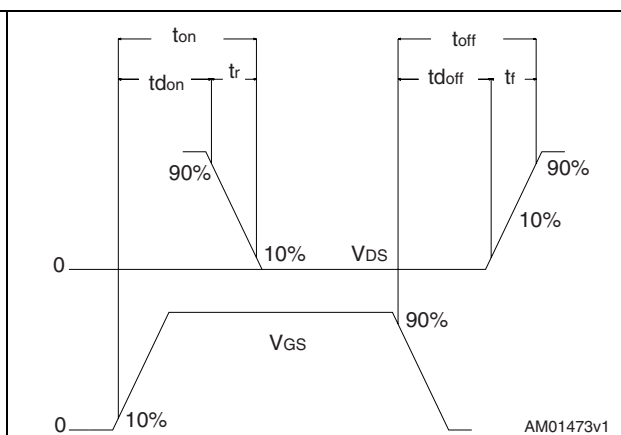


Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing

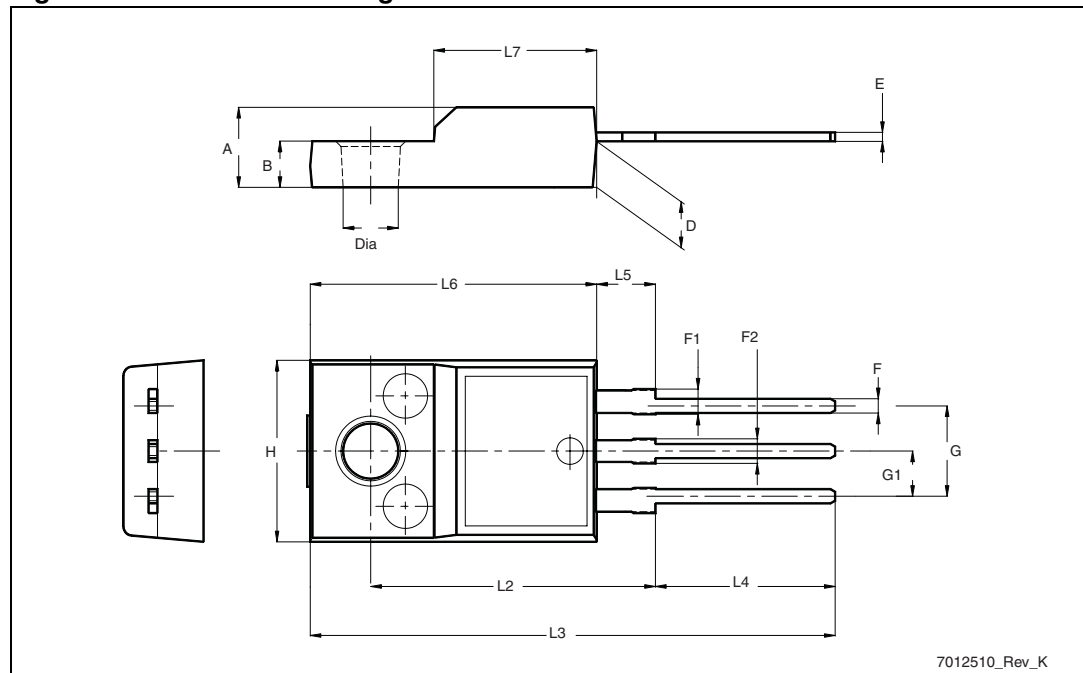


Table 10. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D²PAK footprint^(a)

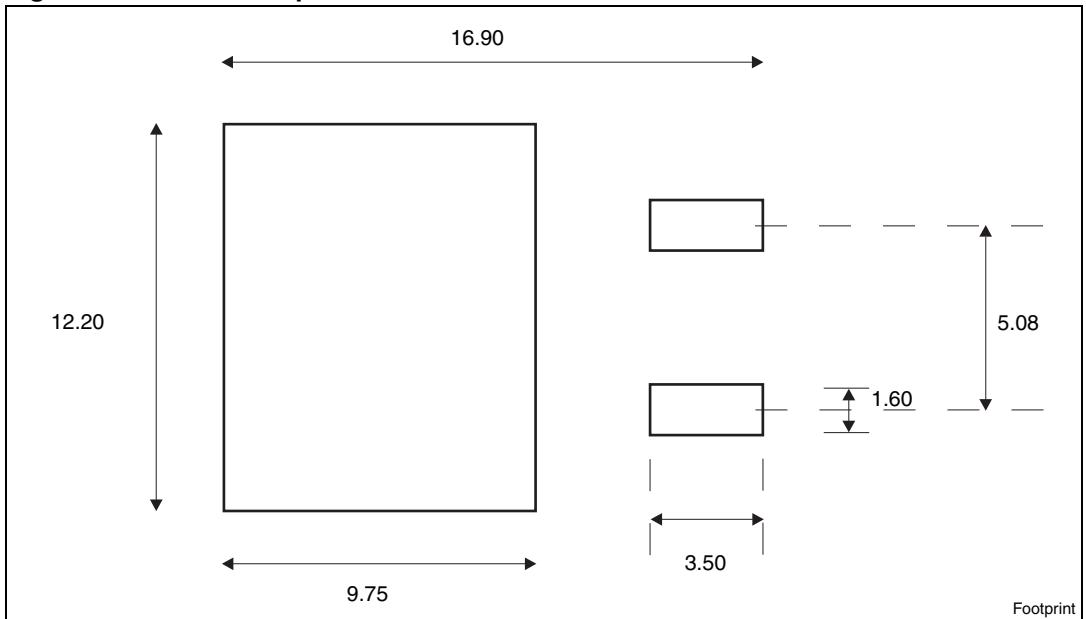
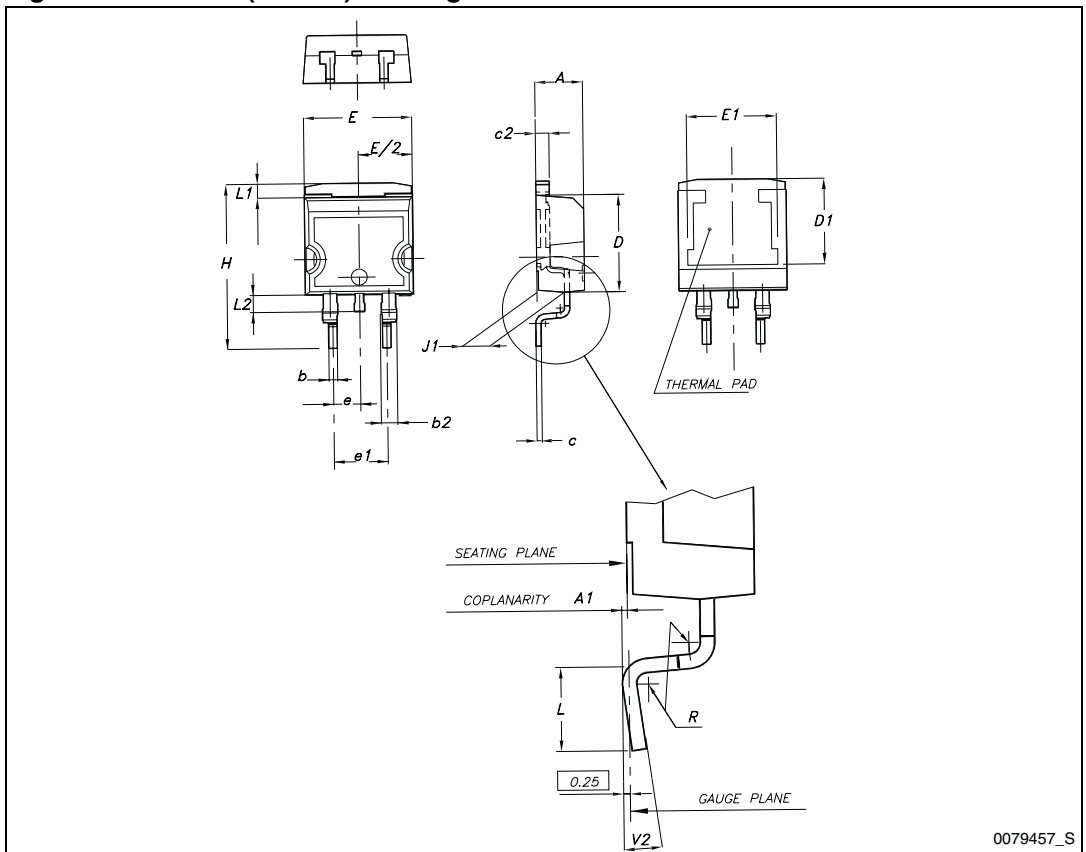


Figure 26. D²PAK (TO-263) drawing



a. All dimension are in millimeters

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing

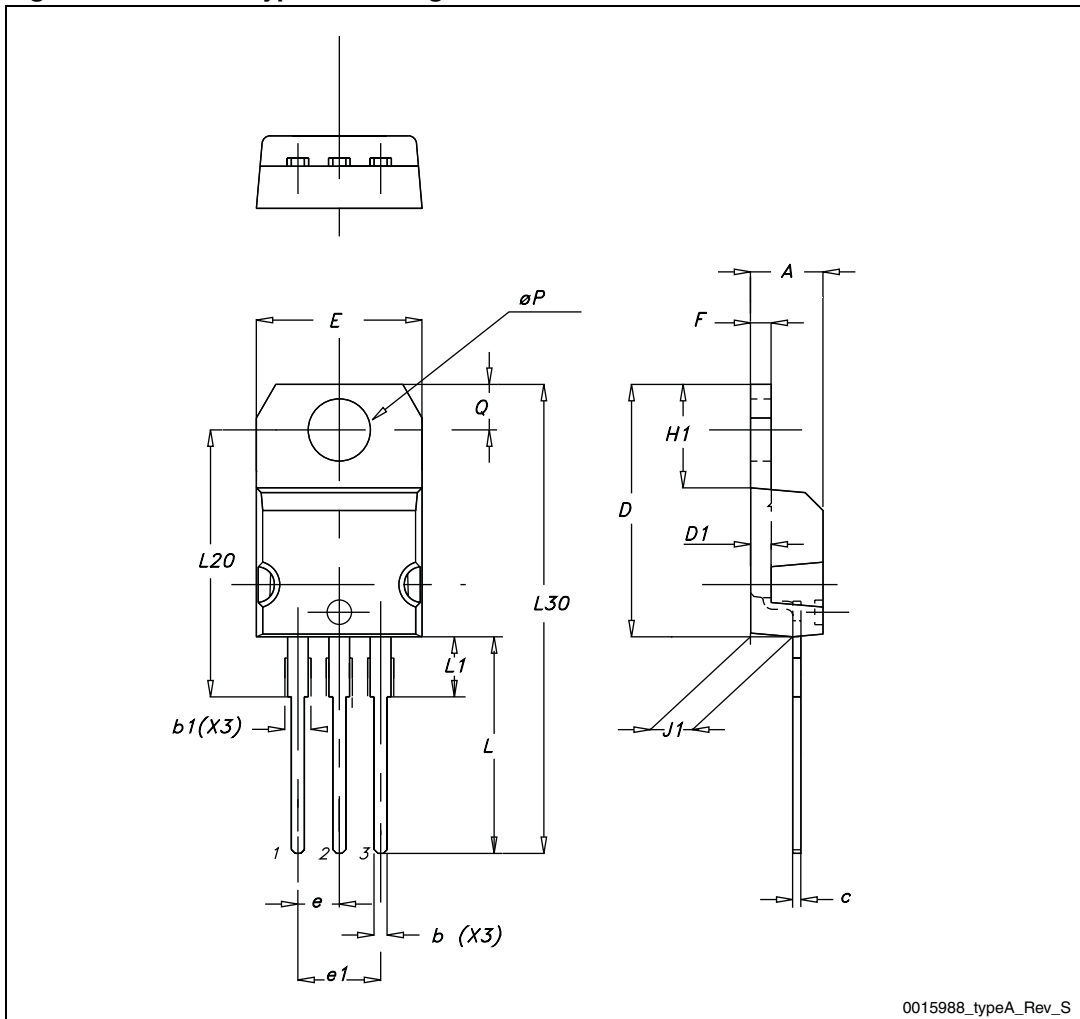
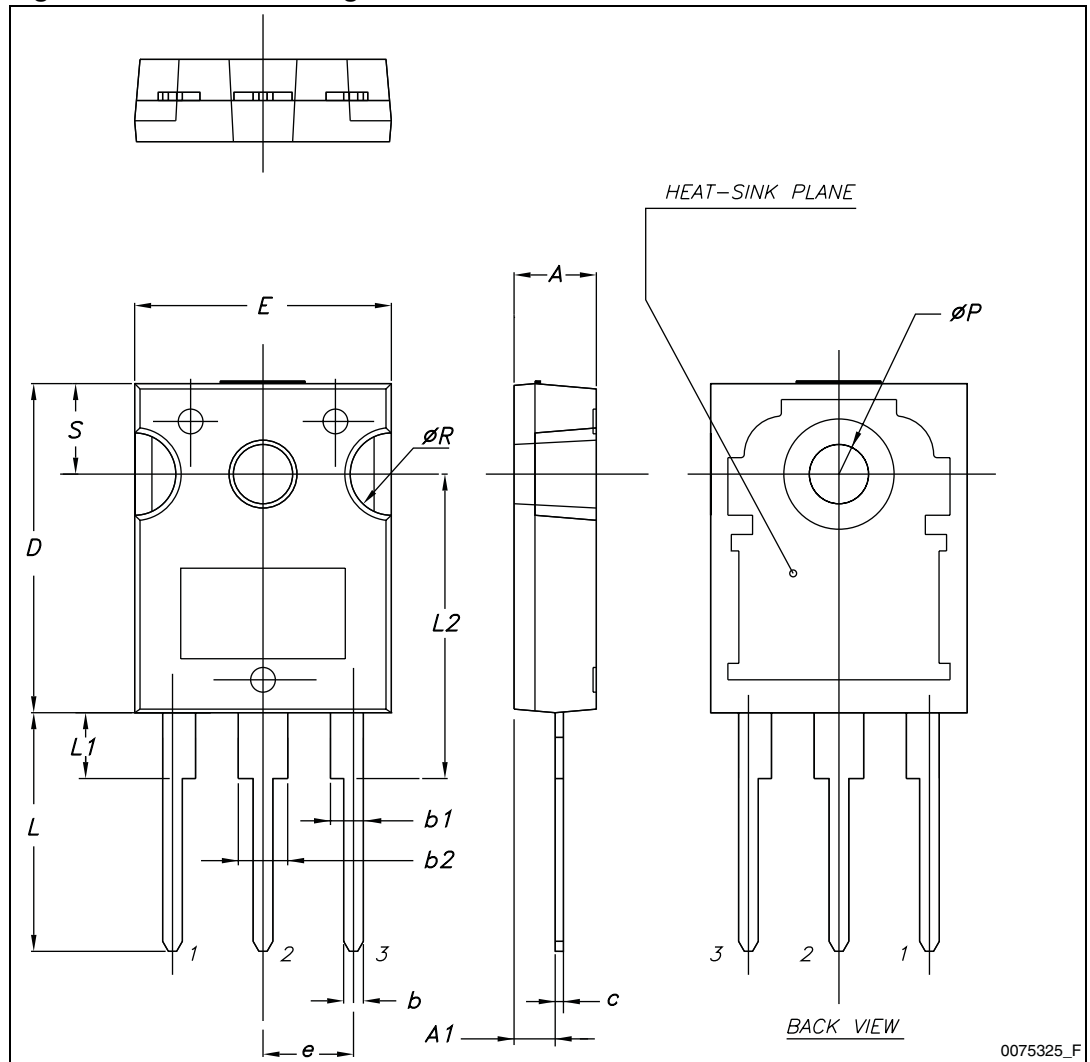


Table 12. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 28. TO-247 drawing

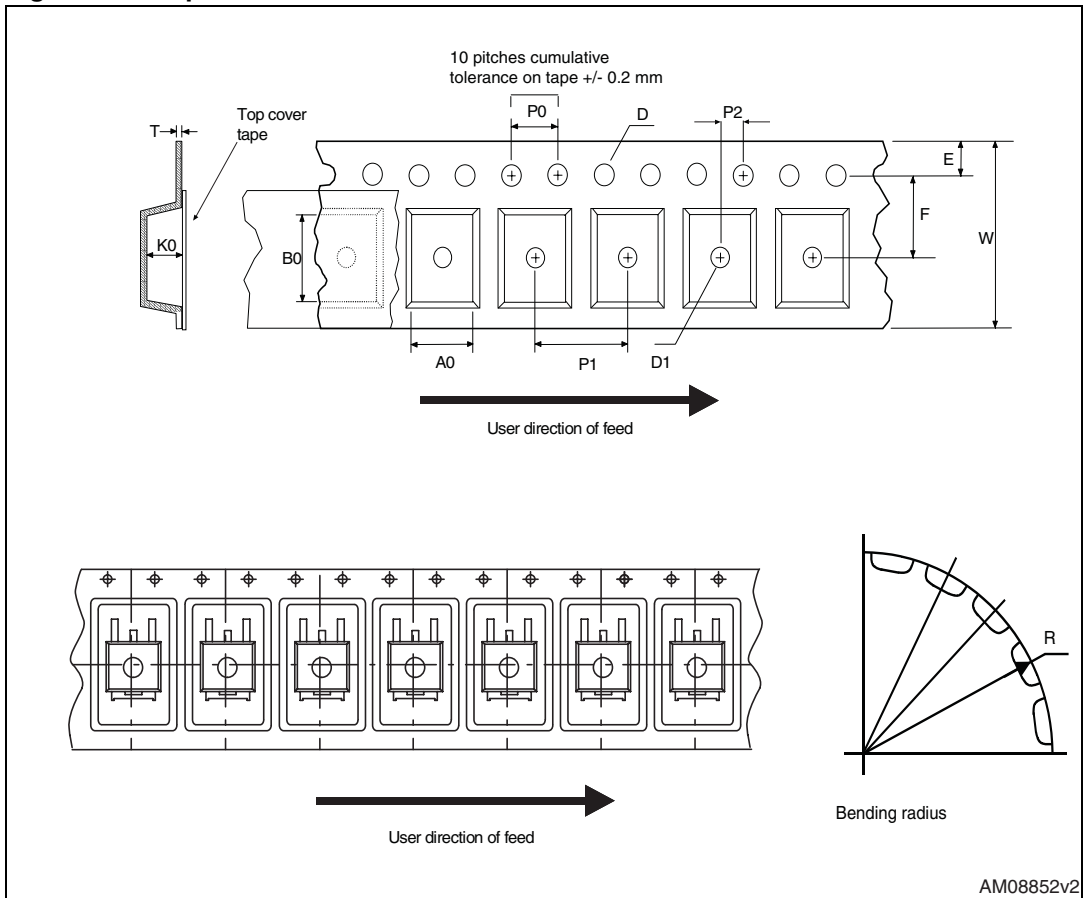


5 Packaging mechanical data

Table 13. D²PAK (TO-263) tape and reel mechanical data

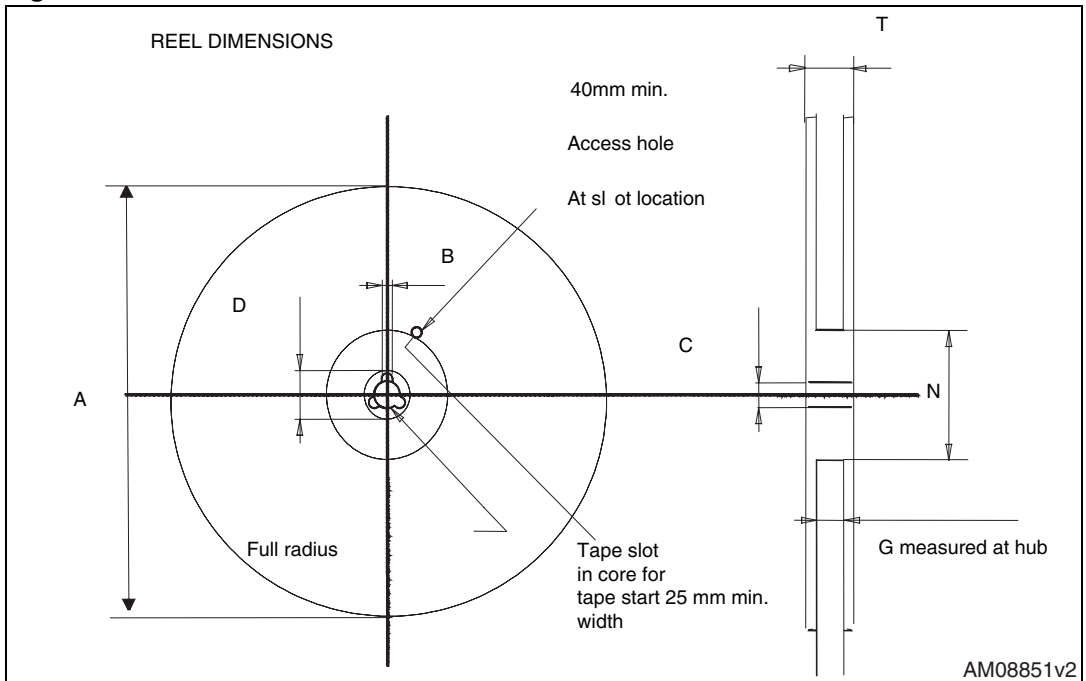
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 29. Tape



AM08852v2

Figure 30. Reel



AM08851v2

6 Revision history

Table 14. Document revision history

Date	Revision	Changes
19-Jul-2010	1	First release.
27-Jun-2011	2	<ul style="list-style-type: none">– Updated Table 6: Dynamic.– Updated Section 2.1: Electrical characteristics (curves).

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